

Please amend the claims as follows:

1. (Currently Amended) A facing targets sputtering device for semiconductor fabrication, comprising:

an air-tight chamber in which an inert gas is admittable and exhaustible;

a pair of target plates placed at opposite ends of said air-tight chamber respectively so as to face each other and form a plasma region therebetween;

a pair of magnets respectively disposed adjacent to said target plates such that magnet poles of different polarities face each other across said plasma region thereby to establish a magnetic field of said plasma region between said target plates;

a substrate holder disposed adjacent to said plasma region, said substrate holder adapted to hold a substrate on which an alloyed thin film is to be deposited;

a chuck heater mounted above the wafer; and

a back-bias power supply coupled to the substrate holder.

2. (Original) A facing targets sputtering device according to claim 1, wherein the back-bias power supply is a DC or an AC electric power source.

3. (Original) A facing targets sputtering device according to claim 1, further comprising a first target power supply coupled to one of the target plates.

4. (Original) A facing targets sputtering device according to claim 3, wherein the first target power supply is a DC or an AC electric power source.

5. (Original) A facing targets sputtering device according to claim 1, further comprising a second target power supply coupled to one of the remaining target plates.
6. (Original) A facing targets sputtering device according to claim 5 ~~4~~, wherein the first and second target power supplies comprises DC and AC electric power sources.
7. (Original) A facing targets sputtering device according to claim 1, further comprising a robot arm to move the wafer.
8. (Original) A facing targets sputtering device according to claim 1, further comprising a magnetron coupled to the chamber.
9. (Withdrawn) A facing targets sputtering device according to claim 1, further comprising a chuck heater mounted above the wafer.
10. (Currently Amended) The facing targets sputtering device ~~apparatus~~ of claim 1, ~~wherein the FTS further comprises~~ comprising first and second targets mounted in parallel.
11. (Currently Amended) The facing targets sputtering device ~~apparatus~~ of claim 10, further comprising magnets positioned between the first and second targets.
12. (Currently Amended) The facing targets sputtering device ~~apparatus~~ of claim 10, further comprising a power supply coupled to the magnets and the targets.

13. (Currently Amended) The facing targets sputtering device apparatus of claim 10, wherein the substrate ~~is~~ are positioned perpendicularly to the planes of the targets.

14. (Withdrawn) The facing targets sputtering device apparatus of claim 13, further comprising a substrate holder to secure the substrate.

15. (Currently Amended) The facing targets sputtering device apparatus of claim 1, wherein the substrate comprises a semiconductor layer ~~is a CMOS layer~~.

16. (Currently Amended) A method for sputtering a thin film onto a substrate, comprising:

providing at least one target and a substrate having a film-forming surface portion and a back portion;

creating a magnetic field so that the film-forming surface portion is placed in the magnetic field with the magnetic field induced normal to the substrate surface portion

back-biasing the back portion of the substrate;

swinging the wafer using a pendulum; and

sputtering material onto the film-forming surface portion.

17. (Original) A method as in claim 16 including providing a pair of said targets opposed to each other where the substrate is disposed between the targets.

18. (Withdrawn) A method as in claim 16, further comprising swinging the wafer using a pendulum.

19. (Original) A method as in claim 16, further comprising supporting a chuck from underneath rather than side-way.

20. (Original) A method as in claim 16, further comprising providing a plurality of sources to deposit materials onto the substrate.